

**REMARKS**

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The Office Action dated January 25, 2008, has been received and its contents carefully reviewed.

Claims 1 and 3-5 are withdrawn in this application. Claims 15-25 are rejected by the Examiner. Claim 15 has been amended. Claims 1, 3-5, 15-18 and 20-25 remain pending in this application.

In the Office Action, claims 15-22 are rejected under 35 U.S.C. § 103(a) as being unpatentable over U.S. Patent No. 6,133,967 to Moon (hereinafter "Moon") in view of U.S. Patent No. 5,815,226 to Yamazaki (hereinafter "Yamazaki"). Claims 23-25 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Moon in view of Yamazaki and further in view of U.S. Patent No. 6,545,730 to Hwang (hereinafter "Hwang"). Claims 15-22 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Moon in view of U.S. Patent No. 6,106,907 to Yoshikawa (hereinafter "Yoshikawa") and further in view of Yamazaki. Claims 23-25 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Moon in view of Yoshikawa and Yamazaki further in view of Hwang.

The rejection of claims 15-18 and 20-25 is respectfully traversed and reconsideration is requested. Claims 15-18 and 20-25 are allowable over the cited references in that each of these claims recites a combination of elements including, for example, "a conductive layer formed on the second insulating layer in the first region except the second region overlapping the storage capacitor electrode except both side portions of the storage capacitor electrode in the first region and formed of the same material as a drain electrode of the thin film transistor", "wherein the width of the conductive layer is shorter than the width of the storage capacitor electrode", and "wherein the storage capacitor is formed by overlapping between the conductive layer connected to the pixel electrode and the storage capacitor electrode connected to the gate line, and the only second insulating layer is disposed between the conductive layer and the storage capacitor electrode." None of the cited references teaches or suggests at least these features of the claimed invention.

In particular, Yamazaki does not disclose that the conductive layer is formed of the same material as a drain electrode of the thin film transistor as claimed. Hence Yamazaki does not disclose that the width of the conductive layer, formed of the same material as a drain electrode,

is shorter than the width of the storage capacitor electrode and that the storage capacitor is formed by overlapping between the conductive layer connected to the pixel electrode and the storage capacitor electrode connected to the gate line, and the only second insulating layer is disposed between the conductive layer and the storage capacitor electrode, as claimed. Also, none of the cited references, including Moon, Hwang and Yoshikawa, discloses that the width of the conductive layer is shorter than the width of the storage capacitor electrode and that the only second insulating layer is disposed between the conductive layer and the storage capacitor electrode, as claimed. Accordingly, Applicant respectfully submits that claim 15, and claims 16-18 and 19-25, which depend therefrom, are allowable over the cited references.

Applicants believe the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. § 1.136, and any additional fees required under 37 C.F.R. § 1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. *A duplicate copy of this sheet is enclosed.*

Respectfully submitted,

Dated: **24 April 2008**

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